

DYNAMIC RANDOM ACCESS MEMORY AND FABRICATION THEREOF

DESCRIPTION

CROSS-REFERENCE TO RELATED APPLICATION

[Para 1] The present application is a continuation-in-part (CIP) application of U.S. Patent Application of Serial No. 10/605,199 filed September 15, 2003, which is a CIP application of U.S. Patent Application of Serial No. 10/210,031 filed August 02, 2002. ^{now Patent No. 6,875,653} The entire contents thereof are incorporated herein for reference.

BACKGROUND OF THE INVENTION

[Para 2] Field of the Invention

[Para 3] This invention pertains in general to semiconductor devices, and, more particularly, to cell and array structures of dynamic random access memory (DRAM) and processes for manufacturing the DRAM array. The DRAM cell features a capacitor that has a particularly high electrical capacitance.

[Para 4] Description of the Related Art

[Para 5] In the semiconductor industry, DRAM is one of the most important integrated circuits, which motivates continuing research and development. There is a continuing effort to increase the storage capacity, improve the writing and reading speed, and decrease the device dimensions of a DRAM cell.